

General Purpose Transistor

- Pb-Free Package May be Available. The G-Suffix Denotes a Pb-Free Lead Finish

MMBT3904LT1G

ORDERING INFORMATION

Device	Marking	Shipping
MMBT3904LT1G	1AM	3000/Tape & Reel
MMBT3904LT3G	1AM	10000/Tape & Reel

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V_{CEO}	40	Vdc
Collector-Base Voltage	V_{CBO}	60	Vdc
Emitter-Base Voltage	V_{EBO}	6.0	Vdc
Collector Current — Continuous	I_C	200	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit
Total Device Dissipation FR-5 Board, (1) $T_A = 25^\circ\text{C}$	P_D	225	mW
Derate above 25°C		1.8	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	556	$^\circ\text{C/W}$
Total Device Dissipation Alumina Substrate, (2) $T_A = 25^\circ\text{C}$	P_D	300	mW
Derate above 25°C		2.4	mW/ $^\circ\text{C}$
Thermal Resistance, Junction to Ambient	$R_{\theta JA}$	417	$^\circ\text{C/W}$
Junction and Storage Temperature	T_J, T_{stg}	-55 to +150	$^\circ\text{C}$

DEVICE MARKING

MMBT3904LT1G = 1AM

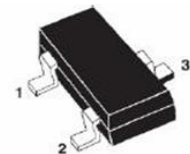
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted.)

Characteristic	Symbol	Min	Max	Unit
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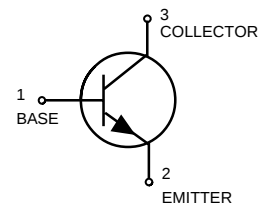
OFF CHARACTERISTICS

Collector-Emitter Breakdown Voltage(3) ($I_C = 1.0 \text{ mAdc}$)	$V_{(BR)CEO}$	40	—	Vdc
Collector-Base Breakdown Voltage ($I_C = 10 \mu\text{Adc}$)	$V_{(BR)CBO}$	60	—	Vdc
Emitter-Base Breakdown Voltage ($I_E = 10 \mu\text{Adc}$)	$V_{(BR)EBO}$	6.0	—	Vdc
Base Cutoff Current ($V_{CE} = 30 \text{ Vdc}, V_{EB} = 3.0 \text{ Vdc},$)	I_{BL}	—	50	nAdc
Collector Cutoff Current ($V_{CE} = 30 \text{ Vdc}, V_{EB} = 3.0 \text{ Vdc}$)	I_{CEX}	—	50	nAdc

- FR-5 = $1.0 \times 0.75 \times 0.062 \text{ in.}$
- Alumina = $0.4 \times 0.3 \times 0.024 \text{ in.}$ 99.5% alumina.
- Pulse Test: Pulse Width $\leq 300 \mu\text{s}$, Duty Cycle $\leq 2.0\%$.



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ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ unless otherwise noted) (Continued)

Characteristic	Symbol	Min	Max	Unit
ON CHARACTERISTICS (3)				
DC Current Gain(1) ($I_C = 0.1\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 1.0\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 10\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 50\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$) ($I_C = 100\text{ mA}$, $V_{CE} = 1.0\text{ Vdc}$)	h_{FE}	40 70 100 60 30	— — 300 — —	—
Collector-Emitter Saturation Voltage ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$)(3) ($I_C = 50\text{ mA}$, $I_B = 5.0\text{ mA}$)	$V_{CE(sat)}$	— —	0.2 0.3	Vdc
Base-Emitter Saturation Voltage(3) ($I_C = 10\text{ mA}$, $I_B = 1.0\text{ mA}$) ($I_C = 50\text{ mA}$, $I_B = 5.0\text{ mA}$)	$V_{BE(sat)}$	0.65 —	0.85 0.95	Vdc

SMALL-SIGNAL CHARACTERISTICS

Current-Gain — Bandwidth Product ($I_C = 10\text{ mA}$, $V_{CE} = 20\text{ Vdc}$, $f = 100\text{ MHz}$)	f_T	300	—	MHz
Output Capacitance ($V_{CB} = 5.0\text{ Vdc}$, $I_E = 0$, $f = 1.0\text{ MHz}$)	C_{obo}	—	4.0	pF
Input Capacitance ($V_{BE} = 0.5\text{ Vdc}$, $I_C = 0$, $f = 1.0\text{ MHz}$)	C_{ibo}	—	8.0	pF
Input Impedance ($V_{CE} = 10\text{ Vdc}$, $I_C = 1.0\text{ mA}$, $f = 1.0\text{ kHz}$)	h_{ie}	1.0	10	k Ω
Voltage Feedback Ratio ($V_{CE} = 10\text{ Vdc}$, $I_C = 1.0\text{ mA}$, $f = 1.0\text{ kHz}$)	h_{re}	0.5	8.0	$\times 10^{-4}$
Small-Signal Current Gain ($V_{CE} = 10\text{ Vdc}$, $I_C = 1.0\text{ mA}$, $f = 1.0\text{ kHz}$)	h_{fe}	100	400	—
Output Admittance ($V_{CE} = 10\text{ Vdc}$, $I_C = 1.0\text{ mA}$, $f = 1.0\text{ kHz}$)	h_{oe}	1.0	40	μmhos
Noise Figure ($V_{CE} = 5.0\text{ Vdc}$, $I_C = 100\mu\text{A}$, $R_S = 1.0\text{ k}\Omega$, $f = 1.0\text{ kHz}$)	NF	—	5.0	dB

SWITCHING CHARACTERISTICS

Delay Time ($V_{CC} = 3.0\text{ Vdc}$, $V_{BE} = -0.5\text{ Vdc}$)	t_d	—	35	ns
Rise Time ($I_C = 10\text{ mA}$, $I_{B1} = 1.0\text{ mA}$)	t_r	—	35	ns
Storage Time ($V_{CC} = 3.0\text{ Vdc}$)	t_s	—	200	ns
Fall Time ($I_C = 10\text{ mA}$, $I_{B1} = I_{B2} = 1.0\text{ mA}$)	t_f	—	50	ns

3. Pulse Test: Pulse Width $\leq 300\mu\text{s}$, Duty Cycle $\leq 2.0\%$.

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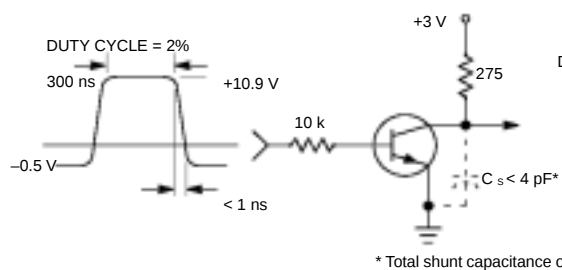


Figure 1. Delay and Rise Time
Equivalent Test Circuit

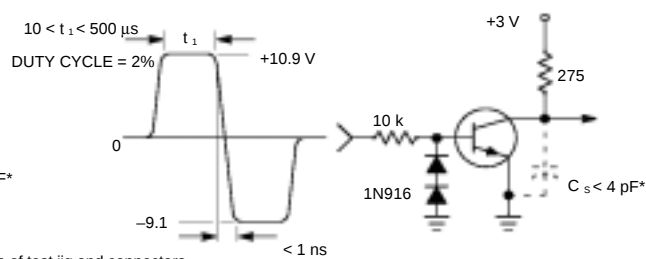


Figure 2. Storage and Fall Time
Equivalent Test Circuit

TYPICAL TRANSIENT CHARACTERISTICS

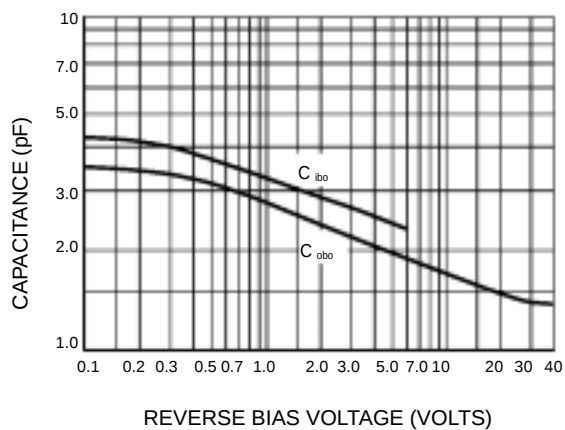


Figure 3. Capacitance

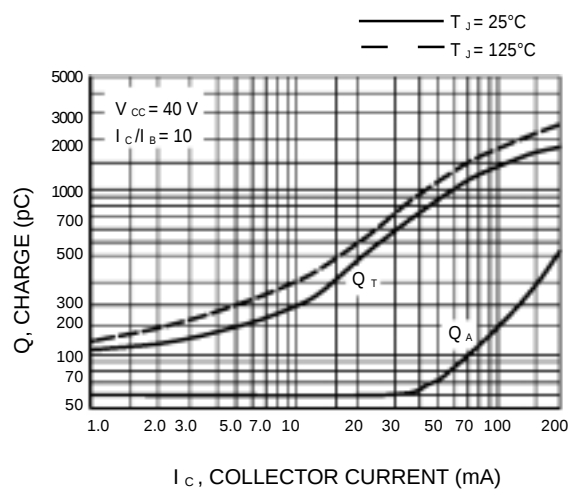


Figure 4. Charge Data

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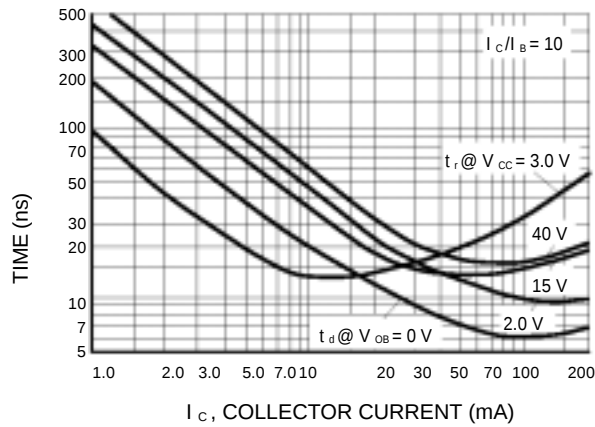


Figure 5. Turn-On Time

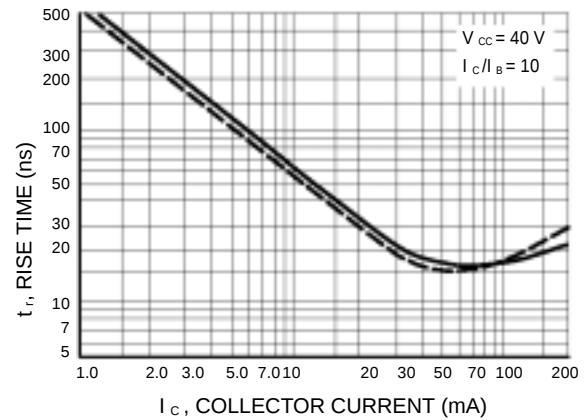


Figure 6. Rise Time

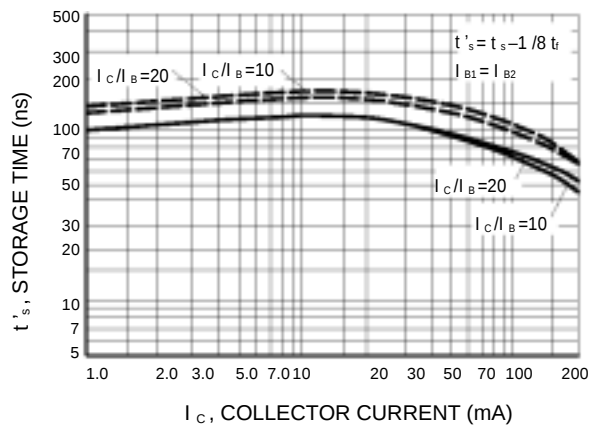


Figure 7. Storage Time

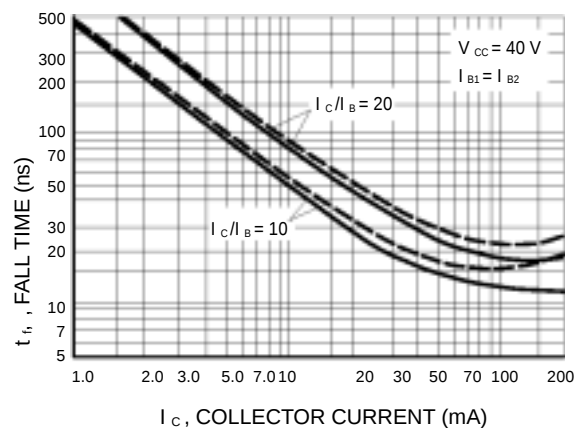


Figure 8. Fall Time

TYPICAL AUDIO SMALL-SIGNAL CHARACTERISTICS

NOISE FIGURE VARIATIONS

($V_{CE} = 5.0 \text{ Vdc}$, $T_A = 25^\circ\text{C}$, Bandwidth = 1.0 Hz)

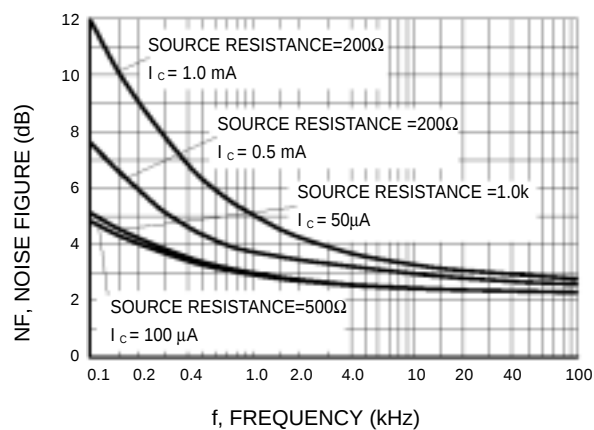


Figure 9.

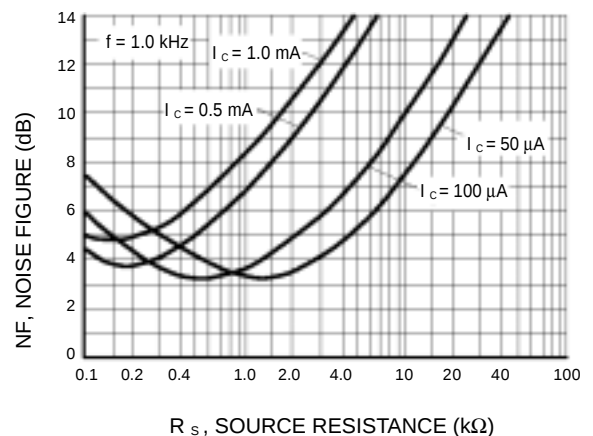


Figure 10.

h PARAMETERS

($V_{CE} = 10\text{ Vdc}$, $f = 1.0\text{ kHz}$, $T_A = 25^\circ\text{C}$)

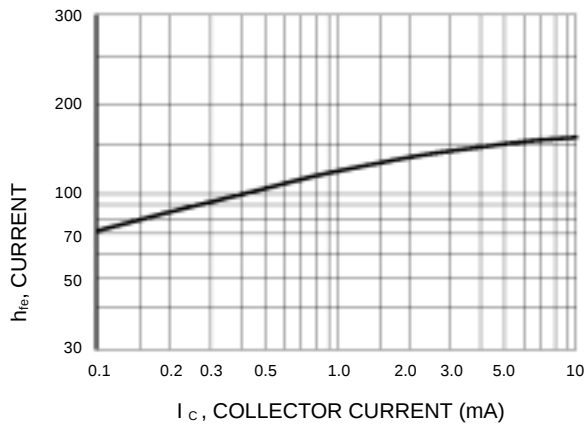


Figure 11. Current Gain

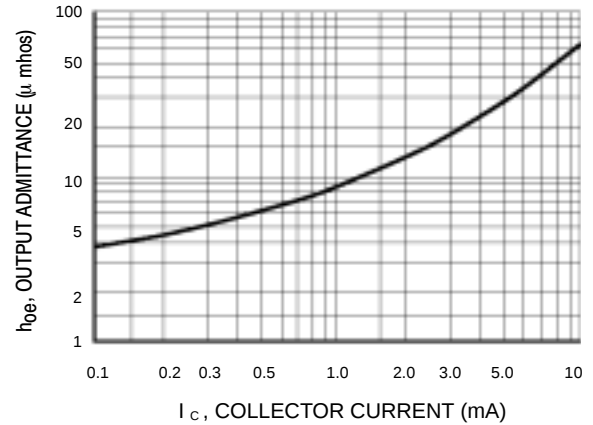


Figure 12. Output Admittance

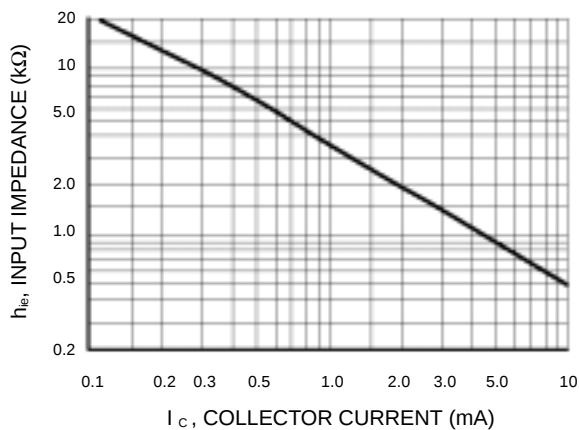


Figure 13. Input Impedance

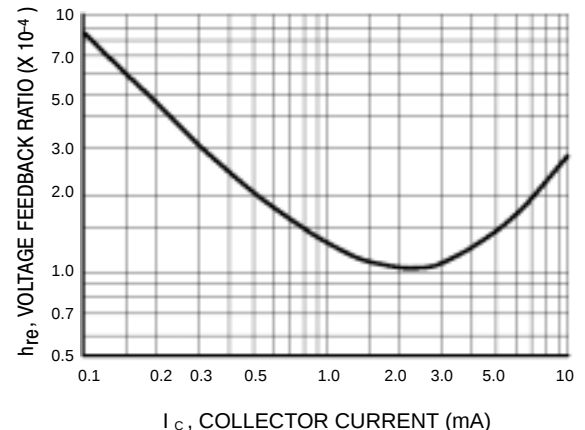


Figure 14. Voltage Feedback Ratio

TYPICAL STATIC CHARACTERISTICS

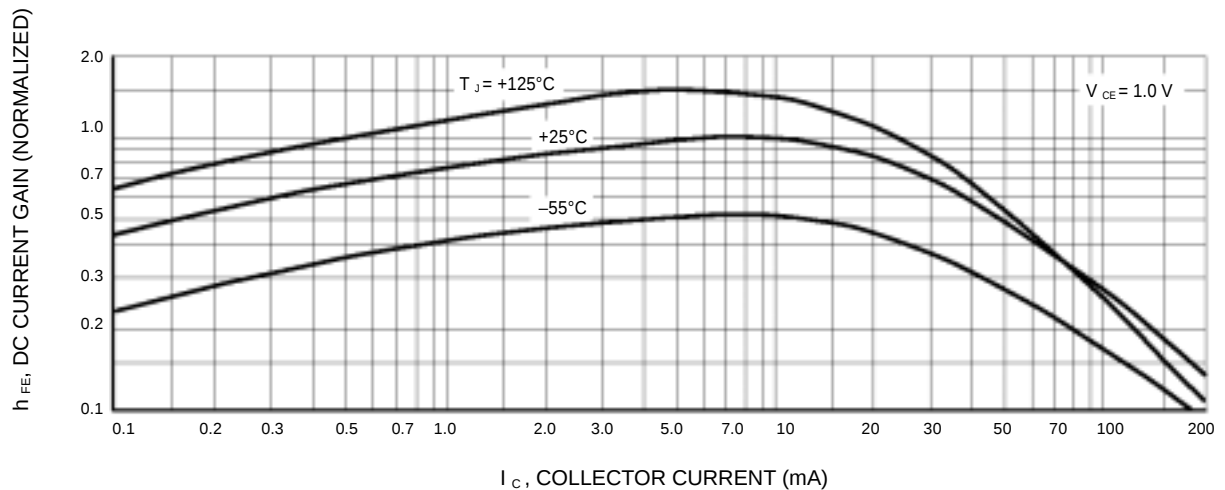


Figure 15. DC Current Gain

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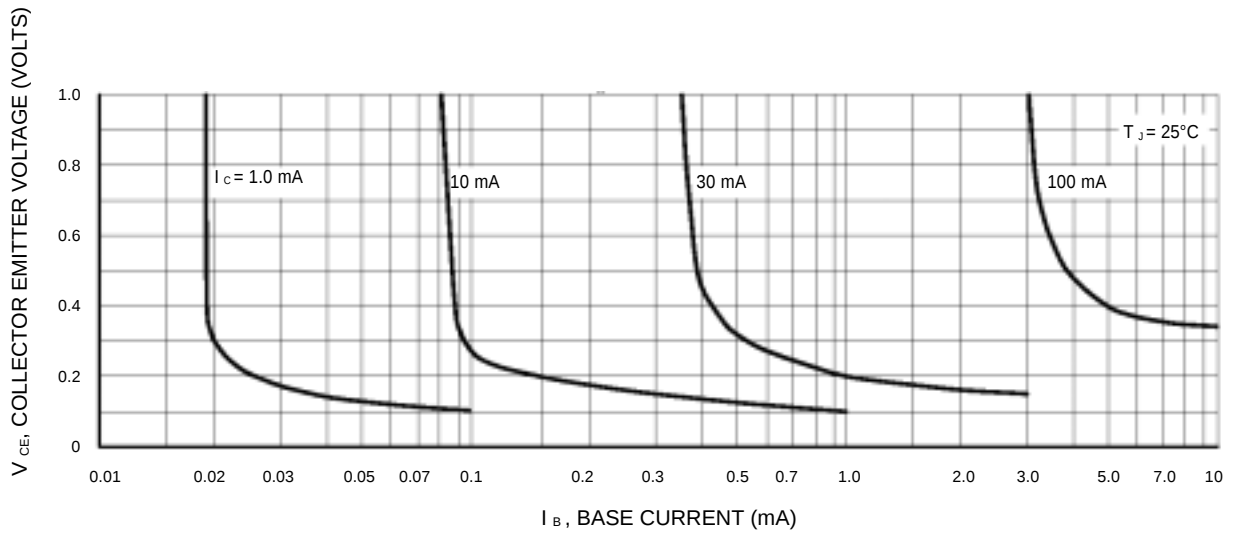


Figure 16. Collector Saturation Region

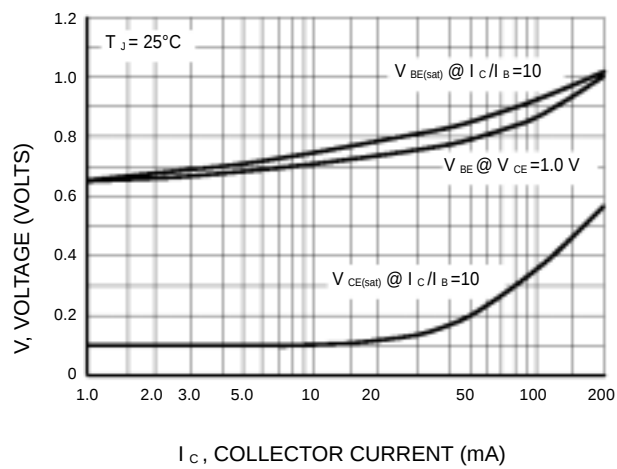


Figure 17. "ON" Voltages

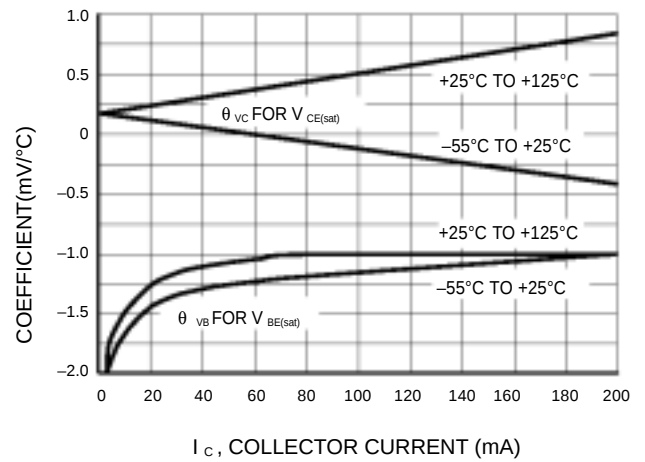
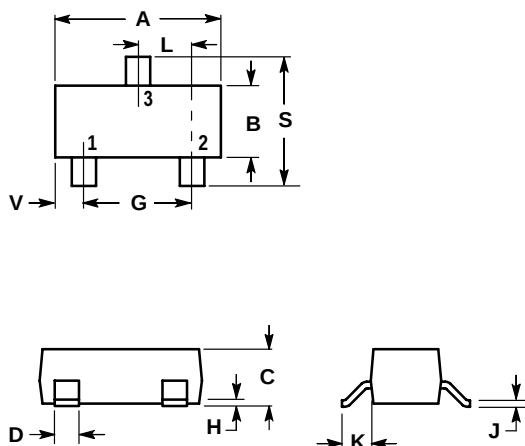


Figure 18. Temperature Coefficients

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NOTES:

1. DIMENSIONING AND TOLERANCING PER ANSI Y14.5M, 1982.
2. CONTROLLING DIMENSION: INCH.

DIM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	0.1102	0.1197	2.80	3.04
B	0.0472	0.0551	1.20	1.40
C	0.0350	0.0440	0.89	1.11
D	0.0150	0.0200	0.37	0.50
G	0.0701	0.0807	1.78	2.04
H	0.0005	0.0040	0.013	0.100
J	0.0034	0.0070	0.085	0.177
K	0.0140	0.0285	0.35	0.69
L	0.0350	0.0401	0.89	1.02
S	0.0830	0.1039	2.10	2.64
V	0.0177	0.0236	0.45	0.60

- PIN 1. BASE
2. EMITTER
3. COLLECTOR

